Renesas Electronics America Inc - R5F212D8SNFP#V2 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	71
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 20x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212d8snfp-v2

1. Overview

1.1 Features

The R8C/2C Group and R8C/2D Group of single-chip MCUs incorporates the R8C/Tiny Series CPU core, employing sophisticated instructions for a high level of efficiency. With 1 Mbyte of address space, and it is capable of executing instructions at high speed. In addition, the CPU core boasts a multiplier for high-speed operation processing.
Power consumption is low, and the supported operating modes allow additional power control. These MCUs also use an anti-noise configuration to reduce emissions of electromagnetic noise and are designed to withstand EMI.
Integration of many peripheral functions, including multifunction timer and serial interface, reduces the number of system components.
Furthermore, the R8C/2D Group has on-chip data flash (1 KB × 2 blocks).
The difference between the R8C/2C Group and R8C/2D Group is only the presence or absence of data flash. Their peripheral functions are the same.

1.1.1 Applications

Electronic household appliances, office equipment, audio equipment, consumer equipment, etc.

1.1.2 Specifications

Tables 1.1 and 1.2 outlines the Specifications for R8C/2C Group and Tables 1.3 and 1.4 outlines the Specifications for R8C/2D Group.

Table 1.1 Specifications for R8C/2C Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C/Tiny series core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to **Table 1.5 Product List for R8C/2C Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3
I/O Ports	Programmable I/O ports	• Input-only: 2 pins • CMOS I/O ports: 71, selectable pull-up resistor • High current drive ports: 8
Clock	Clock generation circuits	3 circuits: XIN clock oscillation circuit (with on-chip feedback resistor), On-chip oscillator (high-speed, low-speed) (high-speed on-chip oscillator has a frequency adjustment function), XCIN clock oscillation circuit (32 kHz) • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• External: 5 sources, Internal: 23 sources, Software: 4 sources • Priority levels: 7 levels
Watchdog Timer		15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RD	16 bits × 2 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 6 pins), reset synchronous PWM mode (output three-phase waveforms (6 pins), sawtooth wave modulation), complementary PWM mode (output three-phase waveforms (6 pins), triangular wave modulation), PWM3 mode (PWM output 2 pins with fixed period)
	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode
	Timer RF	16 bits × 1 (with capture/compare register pin and compare register pin) Input capture mode, output compare mode

1.2 Product List

Table 1.5 lists Product List for R8C/2C Group, Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/2C Group, Table 1.6 lists Product List for R8C/2D Group, and Figure 1.2 shows a Part Number, Memory Size, and Package of R8C/2D Group.

Table 1.5 Product List for R8C/2C Group **Current of Dec. 2007**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks	
R5F212C7SNFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	N version	
R5F212C8SNFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASNFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSNFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		
R5F212C7SDFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	D version	
R5F212C8SDFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASDFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSDFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		
R5F212C7SNXXXFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	N version	Factory programming product(1)
R5F212C8SNXXXFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASNXXXFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSNXXXFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		
R5F212C7SDXXXFP	48 Kbytes	2.5 Kbytes	PLQP0080KB-A	D version	
R5F212C8SDXXXFP	64 Kbytes	3 Kbytes	PLQP0080KB-A		
R5F212CASDXXXFP	96 Kbytes	7 Kbytes	PLQP0080KB-A		
R5F212CCSDXXXFP	128 Kbytes	7.5 Kbytes	PLQP0080KB-A		

NOTE:
1. The user ROM is programmed before shipment.

1.3 Block Diagram

Figure 1.3 shows a Block Diagram.

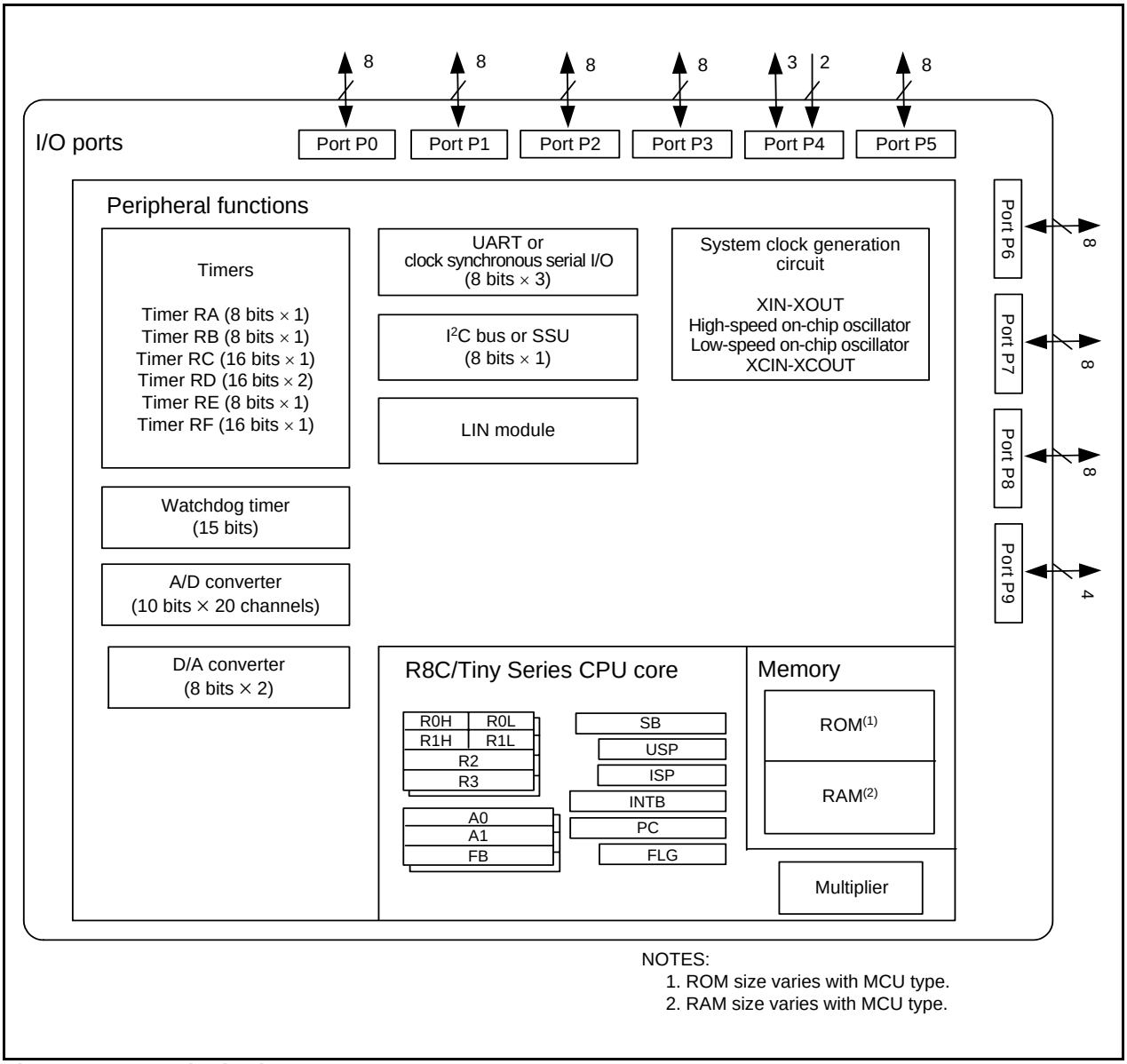


Figure 1.3 Block Diagram

Table 1.8 Pin Name Information by Pin Number (2)

Pin Number	Control Pin	Port	I/O Pin Functions for of Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter
46		P6_7	$\overline{INT3}$		RXD1			
47		P6_5			(CLK1)(1) /CLK2			
48		P6_4			RXD2			
49		P6_3			TXD2			
50		P3_1		TRBO				
51		P3_0		TRAO				
52		P3_6	($\overline{INT1}$)(1)					
53		P3_2	($\overline{INT2}$)(1)					
54		P1_3	$\overline{KI3}$					AN11
55		P1_2	$\overline{KI2}$					AN10
56		P1_1	$\overline{KI1}$					AN9
57		P1_0	$\overline{KI0}$					AN8
58		P7_7						AN19
59		P7_6						AN18
60		P7_5						AN17
61		P7_4						AN16
62		P7_3						AN15
63		P7_2						AN14
64		P7_1						AN13
65		P7_0						AN12
66		P0_0						AN7
67		P0_1						AN6
68		P0_2						AN5
69		P0_3						AN4
70		P0_4						AN3
71		P6_2						
72		P6_1						
73		P0_5			CLK1			AN2
74		P0_6						AN1/DA0
75	VSS/AVSS							
76		P0_7						AN0/DA1
77	VREF							
78	VCC/AVCC							
79		P3_7				SSO		
80		P3_5				SSCK	SCL	

NOTE:
1. Can be assigned to the pin in parentheses by a program.

Table 1.10 Pin Functions (2)

Item	Pin Name	I/O Type	Description
A/D converter	AN0 to AN19	I	Analog input pins to A/D converter
D/A converter	DA0 to DA1	O	D/A converter output pins
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_3 to P4_5, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_3	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P2_0 to P2_7 also function as LED drive ports.
Input port	P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupt are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

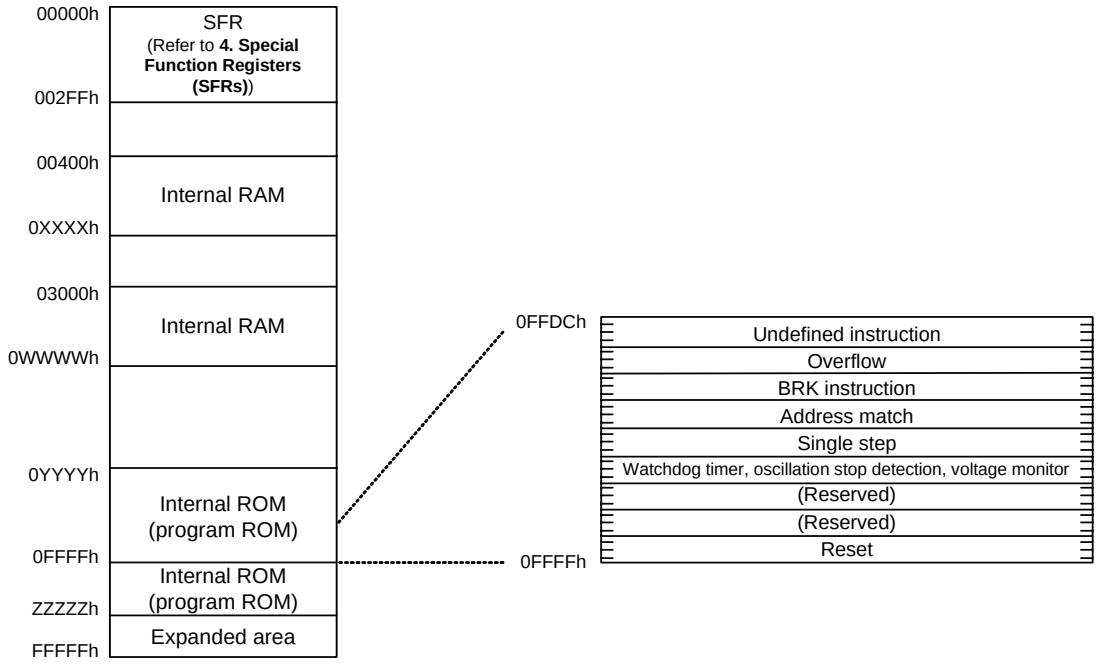
2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/2C Group

Figure 3.1 is a Memory Map of R8C/2C Group. The R8C/2C group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



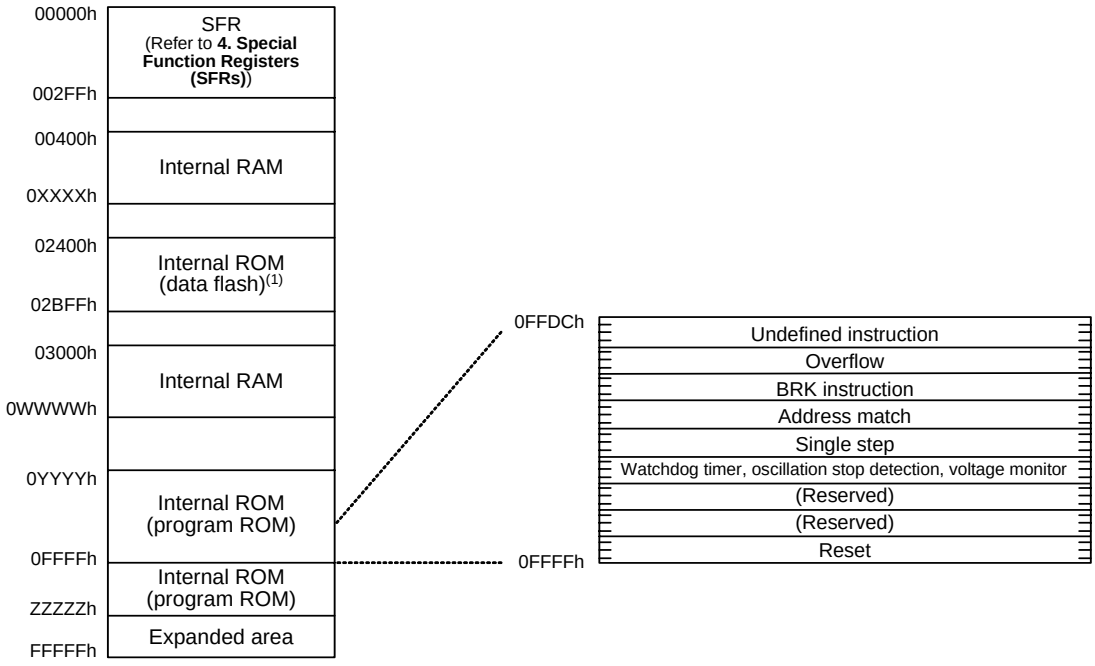
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Internal ROM			Internal RAM		
Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0WWWWh
48 Kbytes	04000h	–	2.5 Kbytes	00DFFh	–
64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	–
96 Kbytes	04000h	1BFFFh	7 Kbytes	011FFh	03DFFh
128 Kbytes	04000h	23FFFh	7.5 Kbytes	011FFh	03FFFh

Figure 3.1 Memory Map of R8C/2C Group

3.2 R8C/2D Group

Figure 3.2 is a Memory Map of R8C/2D Group. The R8C/2D group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Internal ROM			Internal RAM		
Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0WWWWh
48 Kbytes	04000h	–	2.5 Kbytes	00DFFh	–
64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	–
96 Kbytes	04000h	1BFFFh	7 Kbytes	011FFh	03DFFh
128 Kbytes	04000h	23FFFh	7.5 Kbytes	011FFh	03FFFh

Figure 3.2 Memory Map of R8C/2D Group

Table 4.2 SFR Information (2)[1]

Address	Register	Symbol	After reset
0040h			
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
0049h	Timer RD1 Interrupt Control Register	TRD1IC	XXXXX000b
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh			
004Fh	SSU/IIC Interrupt Control Register[2]	SSUIC / IICIC	XXXXX000b
0050h	Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RF Interrupt Control Register	TRFIC	XXXXX000b
005Ch	Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
005Fh	Capture Interrupt Control Register	CAPIC	XXXXX000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. Selected by the IICSEL bit in the PMR register.

Table 4.8 SFR Information (8)(1)

Address	Register	Symbol	After reset
01C0h			
01C1h			
01C2h			
01C3h			
01C4h			
01C5h			
01C6h			
01C7h			
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h			
01D4h			
01D5h			
01D6h			
01D7h			
01D8h			
01D9h			
01DAh			
01DBh			
01DCh			
01DDh			
01DEh			
01DFh			
01E0h			
01E1h			
01E2h			
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h			
01F1h			
01F2h			
01F3h			
01F4h			
01F5h			
01F6h			
01F7h			
01F8h			
01F9h			
01FAh			
01FBh			
01FCh			
01FDh			
01FEh			
01FFh			

NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 5.6 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		–20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. –40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

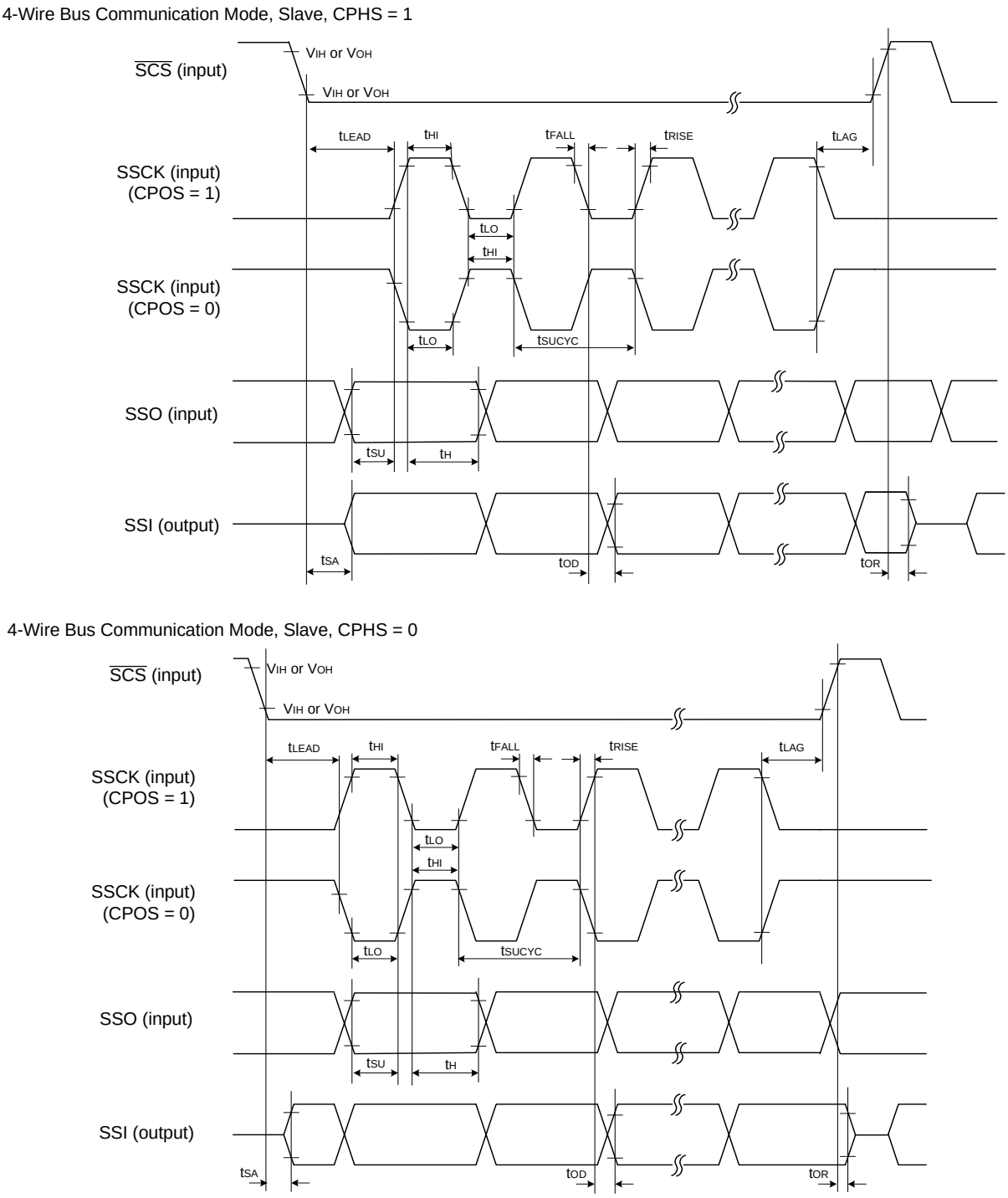


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

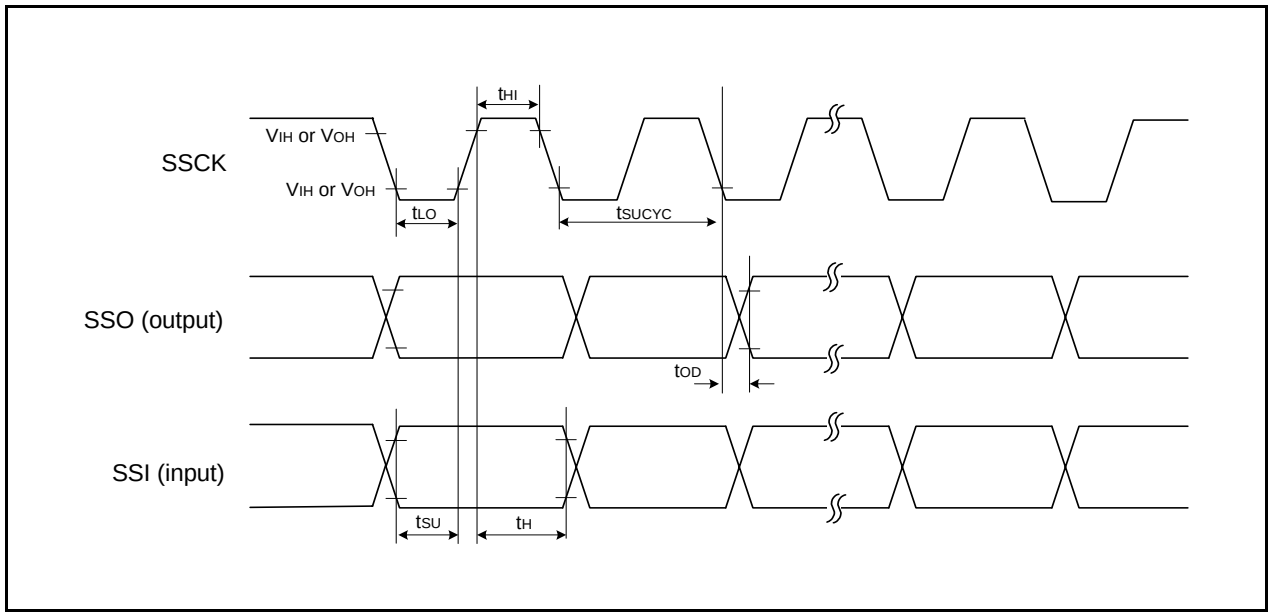


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.16 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = –5 mA		V_{CC} – 2.0	–	V_{CC}	V
			I_{OH} = –200 μA		V_{CC} – 0.5	–	V_{CC}	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = –20 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –5 mA	V_{CC} – 2.0	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = –1 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –500 μA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V		–	–	–5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.17 Electrical Characteristics (2) [Vcc = 5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	12	20	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	16	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	7	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5.5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	6	12	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	150	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	150	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	35	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	30	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	18	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.3	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.7	–	µA

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at Topr = 25°C) [V_{CC} = 5 V]

Table 5.18 XIN Input, XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

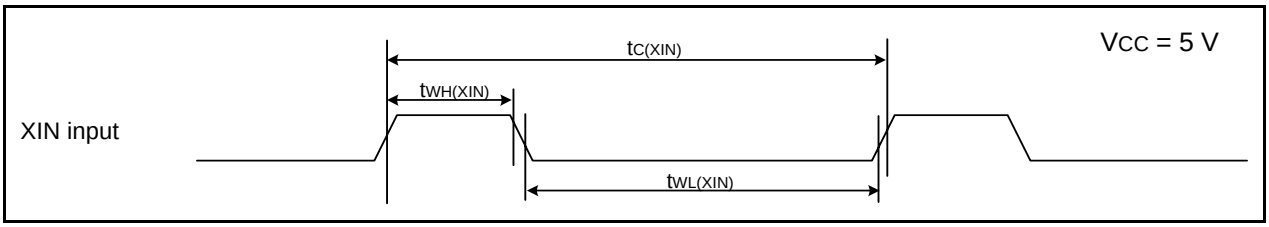


Figure 5.8 XIN Input and XCIN Input Timing Diagram when V_{CC} = 5 V

Table 5.19 TRAIO Input, $\overline{INT1}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

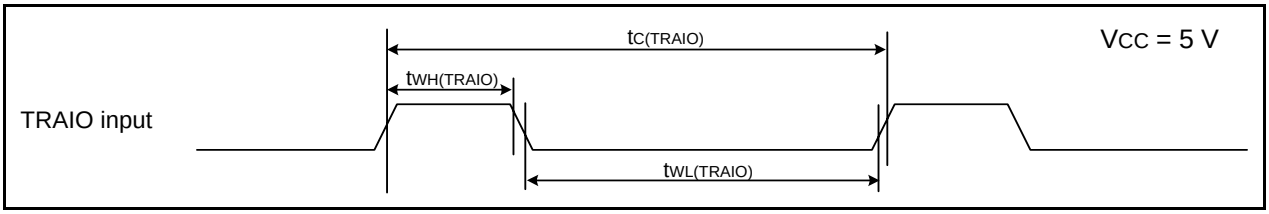


Figure 5.9 TRAIO Input and $\overline{INT1}$ Input Timing Diagram when V_{CC} = 5 V

Table 5.20 TRFI Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRFI)}$	TRFI input cycle time	400(1)	–	ns
$t_{WH(TRFI)}$	TRFI input “H” width	200(2)	–	ns
$t_{WL(TRFI)}$	TRFI input “L” width	200(2)	–	ns

NOTES:
1. When using timer RF input capture mode, adjust the cycle time to (1/timer RF count source frequency × 3) or above.
2. When using timer RF input capture mode, adjust the pulse width to (1/timer RF count source frequency × 1.5) or above.

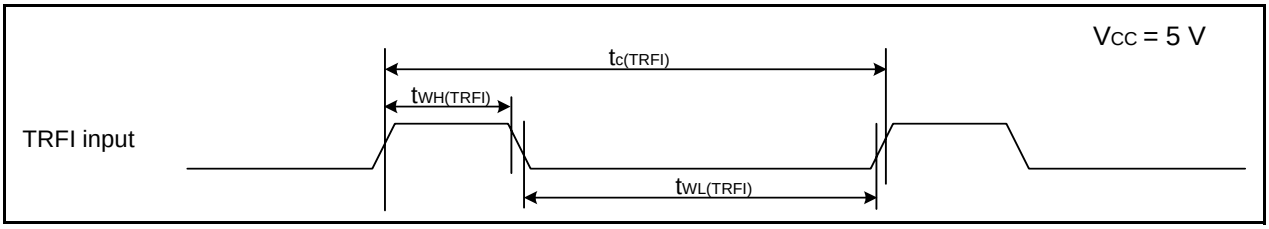


Figure 5.10 TRFI Input Timing Diagram when V_{CC} = 5 V

Table 5.23 Electrical Characteristics (3) [Vcc = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = –1 mA		Vcc – 0.5	–	Vcc	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = –5 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = –1 mA	Vcc – 0.5	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = –0.1 mA	Vcc – 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = –50 µA	Vcc – 0.5	–	Vcc	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. Vcc =2.7 to 3.3 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.24 Electrical Characteristics (4) [Vcc = 3 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	11	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.2	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	145	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	145	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	28	85	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	17	50	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.3	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.1	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.65	3.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.65	–	µA

Table 5.30 Electrical Characteristics (5) [V_{CC} = 2.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P2_0 to P2_7, XOUT	I_{OH} = –1 mA		V_{CC} – 0.5	–	V_{CC}	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = –0.1 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = –50 µA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P2_0 to P2_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRFI, RXD0, RXD1, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.05	0.3	–	V
		$\overline{RESET}$			0.05	0.15	–	V
I_{IH}	Input “H” current		VI = 2.2 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		100	200	600	kΩ
R_{fXIN}	Feedback resistance	XIN			–	5	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	35	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 2.2 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.